

# High temperature ion implantation / high temperature annealing

We do heat treatment according to customer's request. We can perform a series of processes such as high-temperature ion implantation, cap film formation and high-temperature annealing suitable for SiC device fabrication.

## High temperature ion implantation

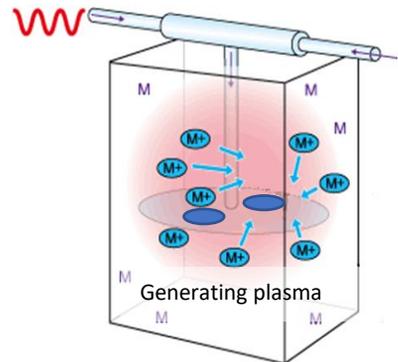
High temperature ion implantation up to 600 °C  
Compatible with small chip to 6-inch sizes  
Effective for reducing implantation damage



## Cap film deposition

React  $C_2H_2$  to form DLC film  
Compatible with small chip to 6-inch sizes  
Effective for reducing surface roughness by annealing treatment

High frequency to generate plasma



## High temperature annealing

Annealing up to 1800 °C  
Compatible with small to 6-inch sizes  
Compatible with various compound semiconductors

